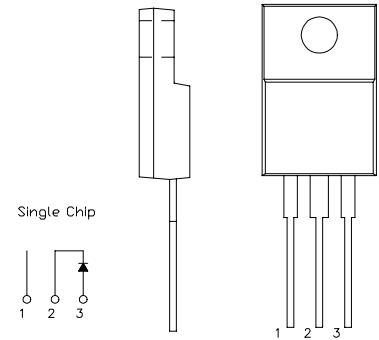


SBD Type : FSH10A10B

OUTLINE DRAWING

FEATURES

- *Similar to TO-220AB Case
- *Fully Molded Isolation
- *Low Forward Voltage Drop
- *Low Power Loss,High Efficiency
- *High Surge Capability
- *Tj=150 °C operation



Maximum Ratings

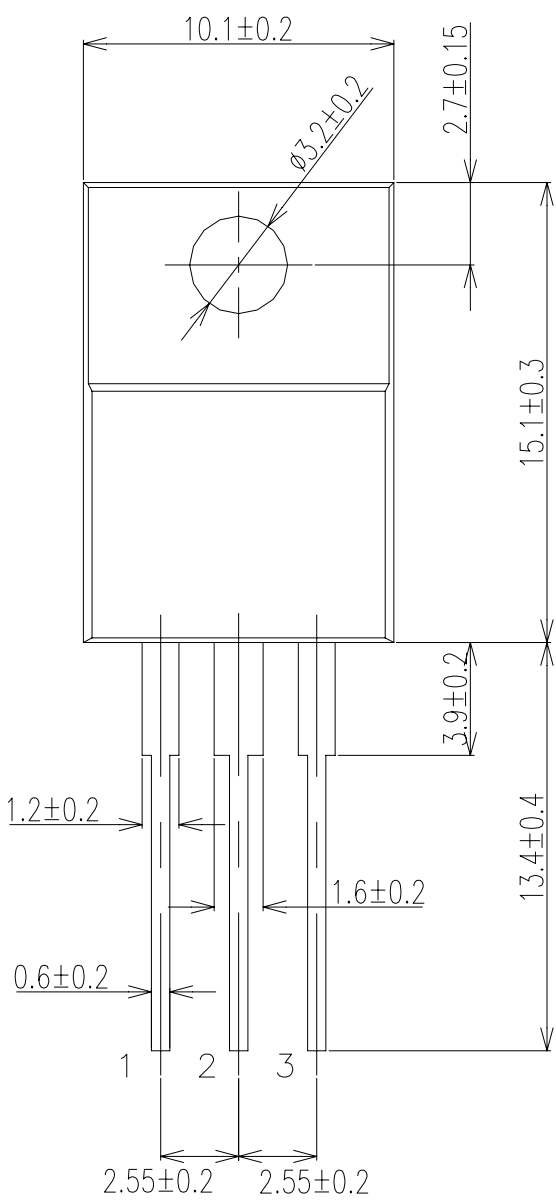
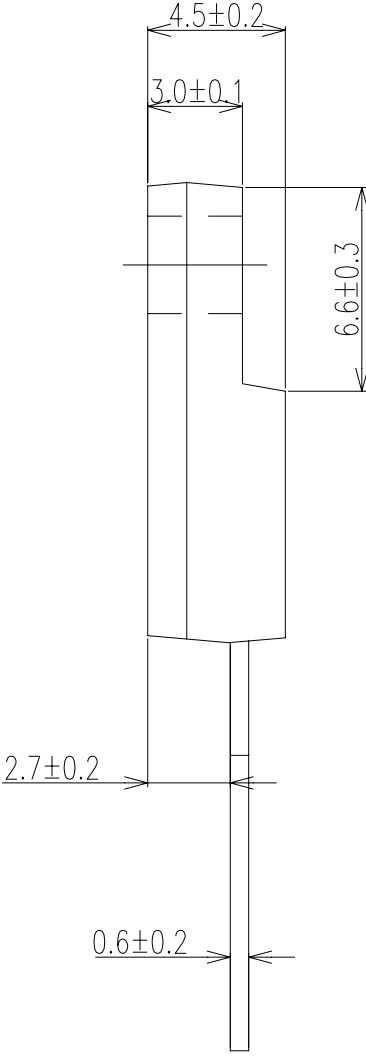
Approx Net Weight: 1.75g

Rating	Symbol	FSH10A10B			Unit
Repetitive Peak Reverse Voltage	V _{RRM}	100			V
Average Rectified Output Current	I _O	10	Tc=120°C	50 Hz half Sine Wave Resistive Load	A
RMS Forward Current	I _{F(RMS)}	15.7			A
Surge Forward Current	I _{FSM}	180	50Hz Half Sine Wave ,1cycle Non-repetitive		A
Operating JunctionTemperature Range	T _{jw}	-40 to +150			°C
Storage Temperature Range	T _{stg}	-40 to +150			°C
Mounting torque	F _{tor}	recommended torque = 0.5			N•m

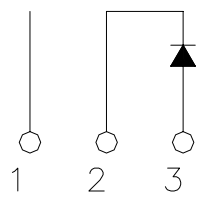
Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	$T_j= 25^{\circ}\text{C}, V_{RM}= V_{RRM}$	-	-	1	mA
Peak Forward Voltage	V_{FM}	$T_j= 25^{\circ}\text{C}, I_{FM}= 10 \text{ A}$	-	-	0.88	V
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	3	°C /W
	$R_{th(c-f)}$	Cace to Fin	-	-	1.5	°C /W

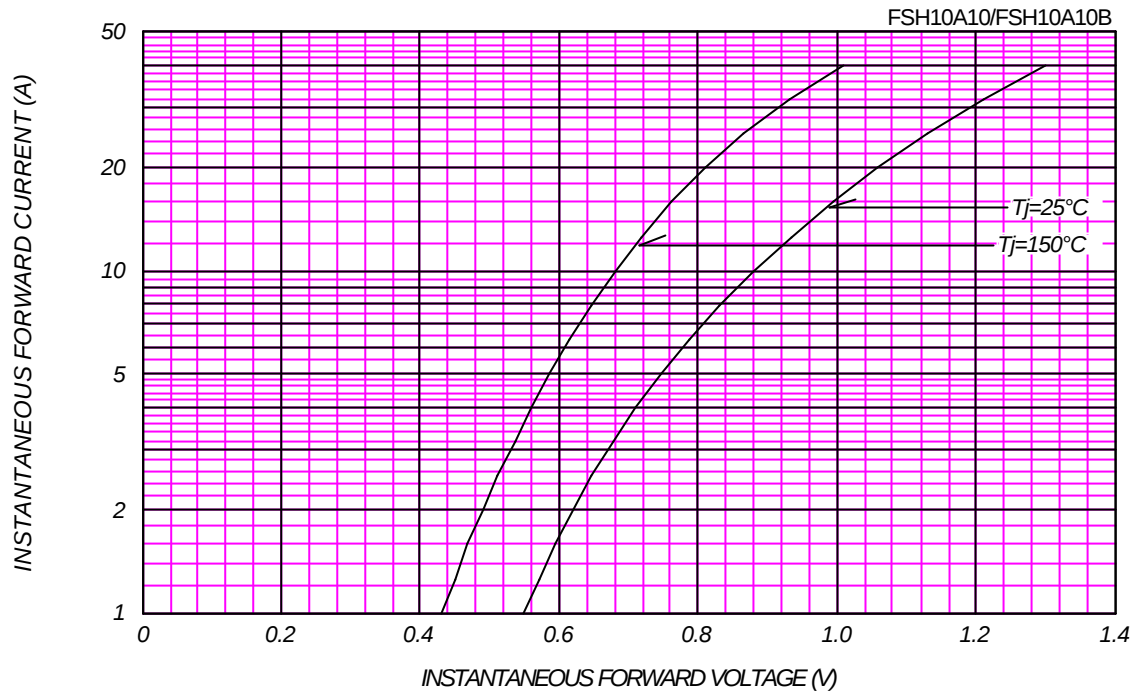
FSH_A_B OUTLINE DRAWING (Dimensions in mm)



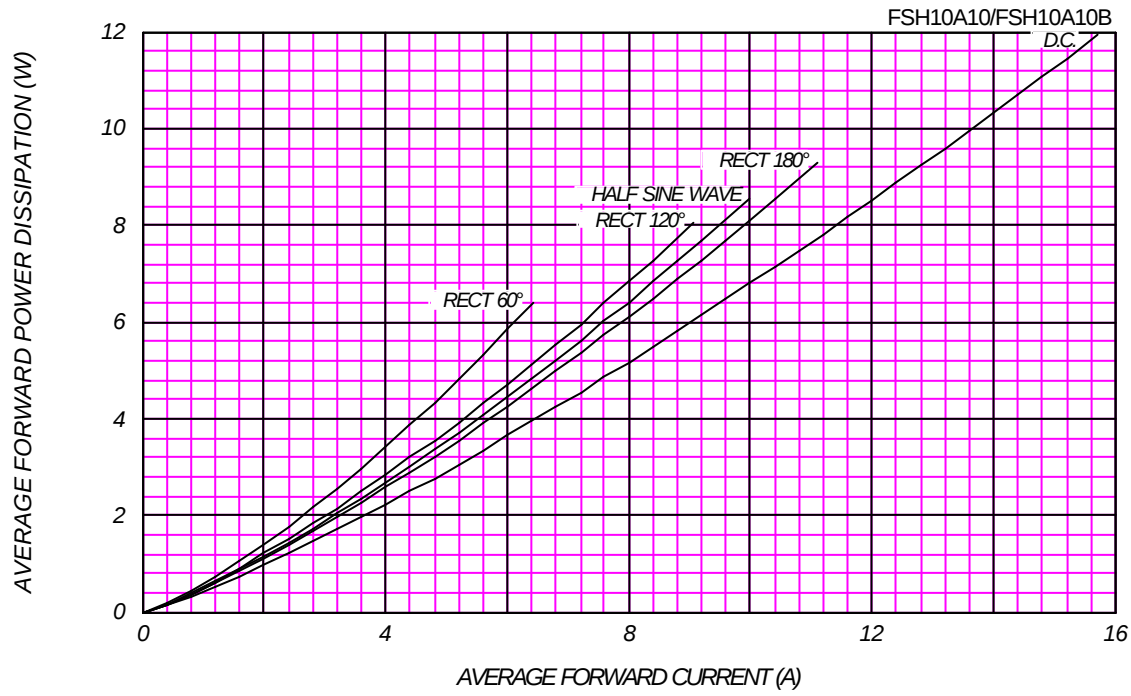
Single Chip



FORWARD CURRENT VS. VOLTAGE



AVERAGE FORWARD POWER DISSIPATION



PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

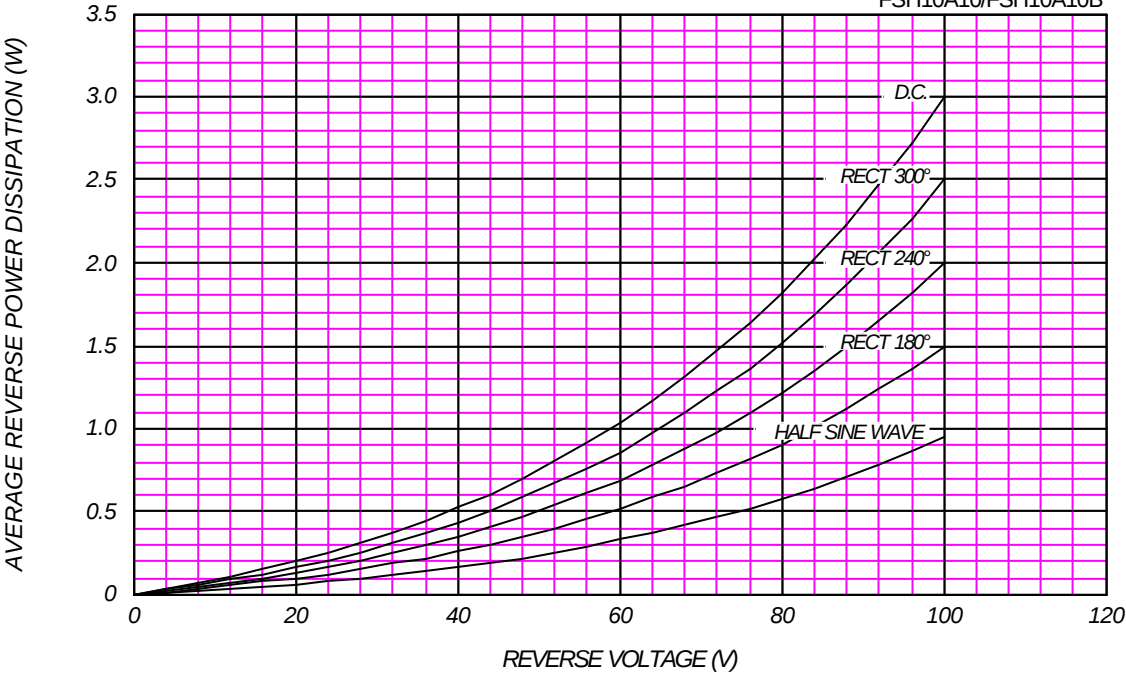
T_j= 150 °C

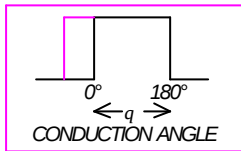
FSH10A10/FSH10A10B



AVERAGE REVERSE POWER DISSIPATION

FSH10A10/FSH10A10B

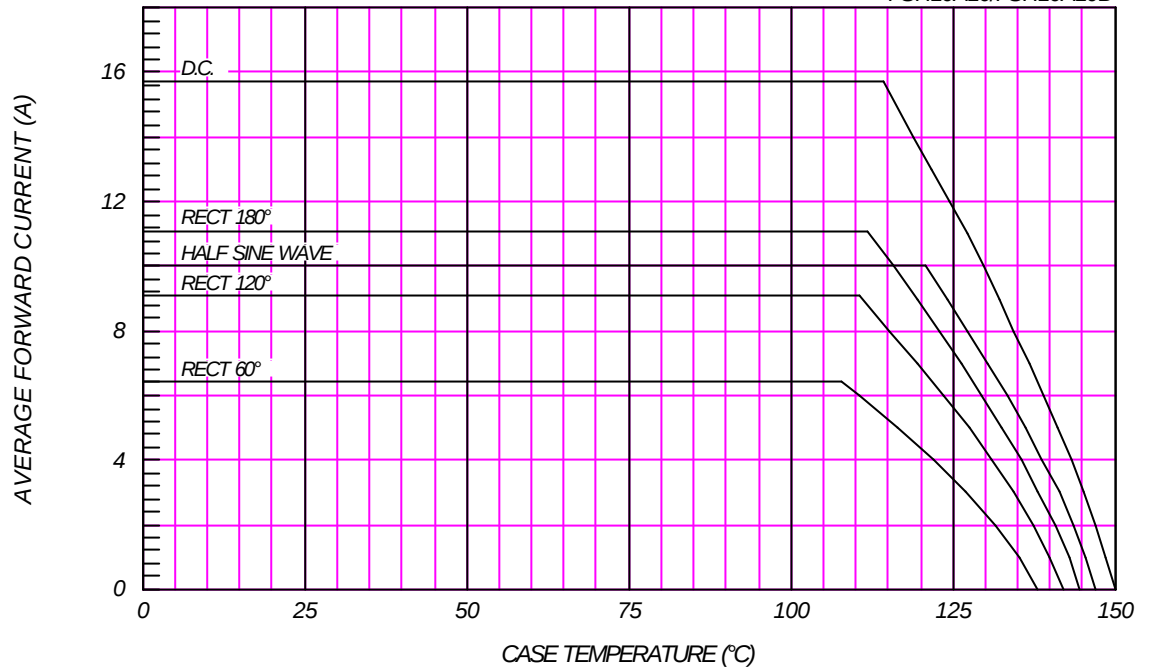




AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE

$V_{RM}=100V$

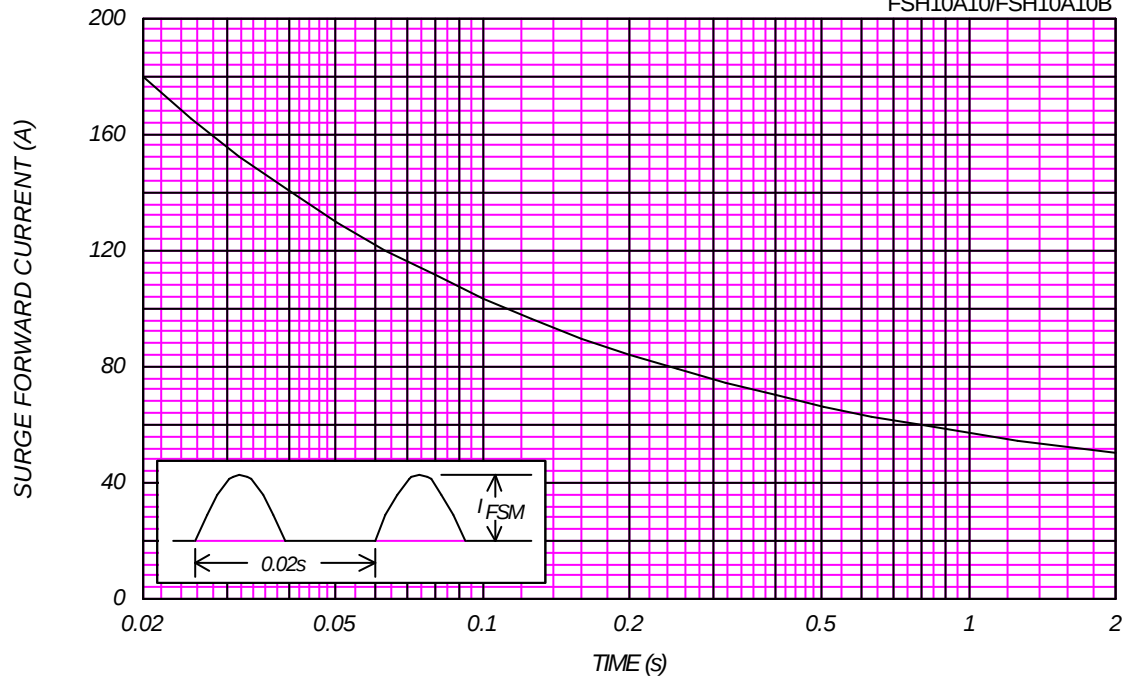
FSH10A10/FSH10A10B



SURGE CURRENT RATINGS

$f=50Hz$, Half Sine Wave, Non-Repetitive, No Load

FSH10A10/FSH10A10B



JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

$T_j=25^{\circ}\text{C}$, $V_m=20\text{mV}_{\text{RMS}}$, $f=100\text{kHz}$, Typical Value

FSH10A10/FSH10A10B

